

**SMBYW01-200**

HIGH EFFICIENCY FAST RECOVERY DIODE

MAIN PRODUCT CHARACTERISTICS

I _{F(AV)}	1 A
V _{RRM}	200 V
V _{F(max)}	0.71 V
T _{j(max)}	150 °C



SMB
(JEDEC DO-214AA)

FEATURES AND BENEFITS

- VERY LOW SWITCHING LOSSES
- LOW FORWARD VOLTAGE DROP BIPOLAR DEVICE
- LOW PEAK FORWARD VOLTAGE FOR TELE-COM TRANSIENT OPERATION SUCH AS IN LIGHTING PROTECTION CIRCUITS

DESCRIPTION

Single chip rectifier suited to Switch Mode Power Supplies and high frequency DC to DC converters.

Packaged in SMB, this surface mount device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit
V _{RRM}	Repetitive peak reverse voltage	200	V
I _{F(RMS)}	RMS forward current	8	A
I _{F(AV)}	Average forward current	1	A
I _{FSM}	Surge non repetitive forward current	tp=10ms sinusoidal	A
T _{stg}	Storage and junction temperature range	- 65 to + 150	°C
T _j	Maximum operating junction temperature	150	°C

SMBYW01-200

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R _{th} (j-l)	Junction to lead	13	°C/W

STATIC ELECTRICAL CHARACTERISTICS

Symbol	Parameters	Test Conditions		Min.	Typ.	Max.	Unit
V _F *	Forward voltage drop	T _j = 25°C	I _F = 1 A			0.9	/
		T _j = 150°C	I _F = 1 A		0.65	0.71	
I _R **	Reverse leakage current	T _j = 25°C	V _R = V _{RRM}			3	μA
		T _j = 125°C			180	400	

Pulse test : * tp = 380 μs, δ < 2 %

** tp = 5 ms, δ < 2 %

To evaluate the maximum conduction losses use the following equation :
 $P = 0.58 \times I_{F(AV)} + 0.118 \times I_F^2(RMS)$

RECOVERY CHARACTERISTICS

Symbol	Test Conditions			Min.	Typ.	Max.	Unit
t _{rr}	T _j = 25°C	I _F = 0.5 A	I _{rr} = 0.25 A	I _R = 1A		25	ns
		I _F = 1 A	dI _F /dt = - 50 A/μs	V _R = 30V		25	
t _{fr}	T _j = 25°C	I _F = 1A	dI _F /dt = 100 A/μs			25	ns
V _{FP}	T _j = 25°C	I _F = 1A	dI _F /dt = 100 A/μs			5	V

Fig. 1: Average forward power dissipation versus average forward current .

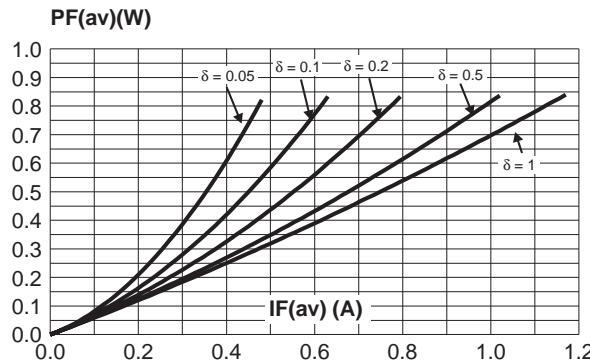


Fig. 3: Average forward current versus ambient temperature ($\delta=0.5$).

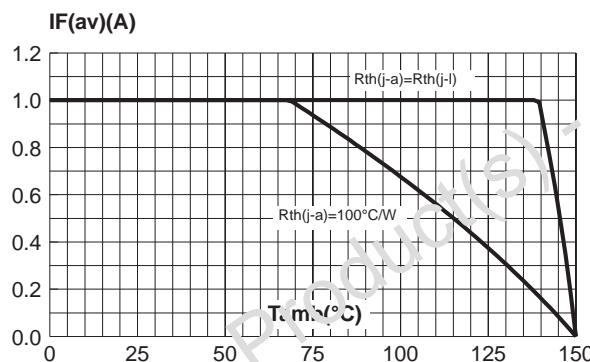


Fig. 5: Variation of thermal impedance junction to ambient versus pulse duration (recommended pad layout, epoxy FR4, e(Cu)=35μm).

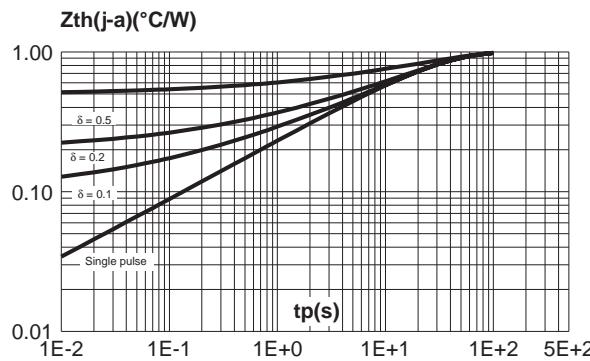


Fig. 2: Peak current versus form factor.

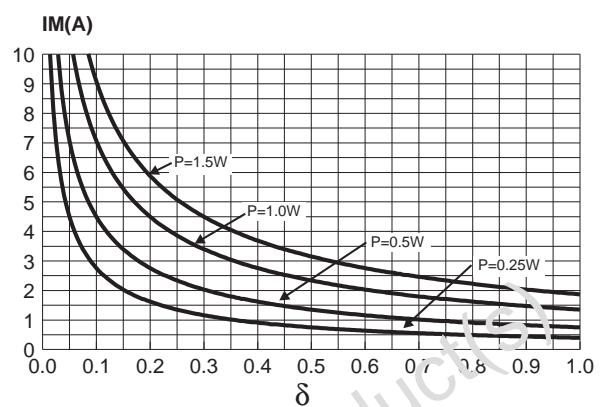


Fig. 4: Non repetitive surge peak forward current versus overcurrent configuration.

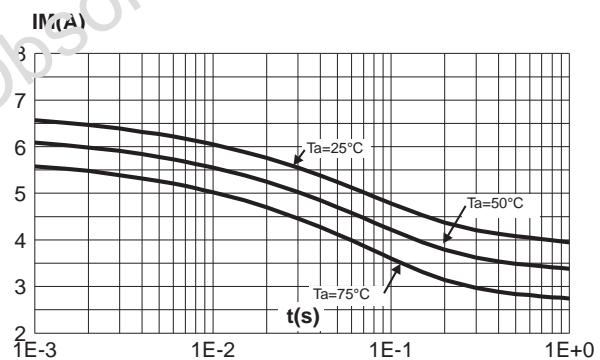
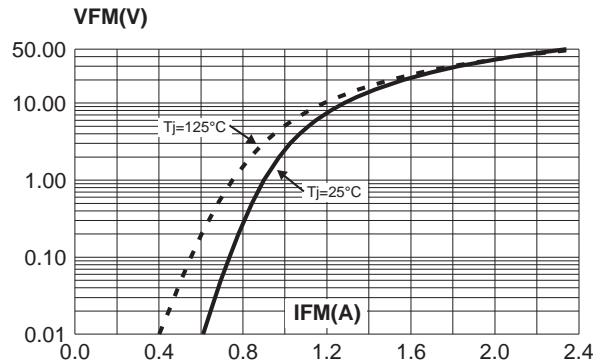


Fig 6: Forward voltage drop versus forward current (maximum values).



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Fig. 7: Junction capacitance versus reverse voltage applied (typical values).

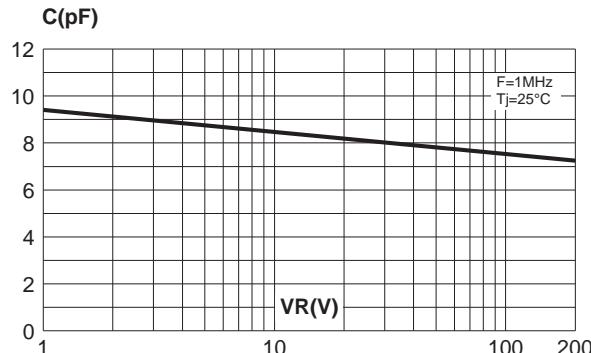


Fig. 9: Reverse recovery time versus dI_F/dt .

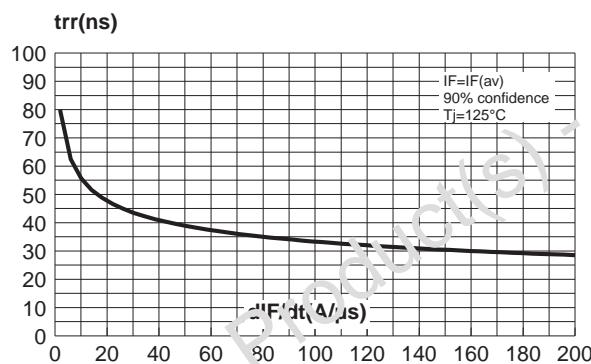


Fig. 11: Dynamic parameters versus junction temperature.

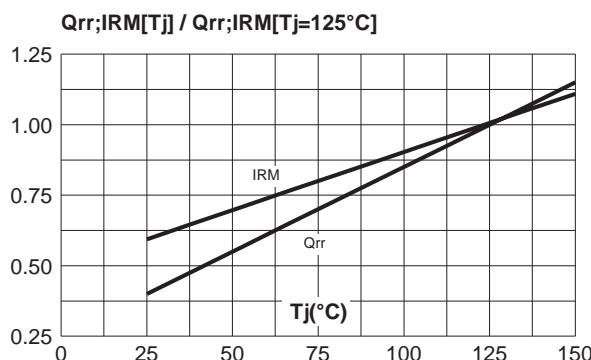


Fig. 8: Reverse recovery current versus dI_F/dt .

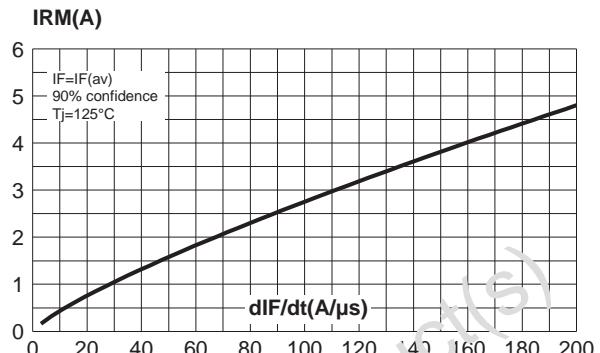


Fig. 10: Reverse recovery charges versus dI_F/dt .

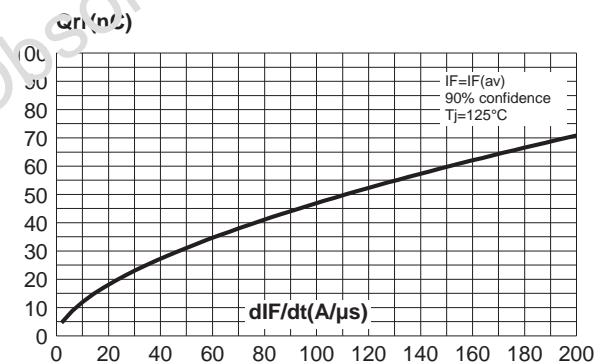
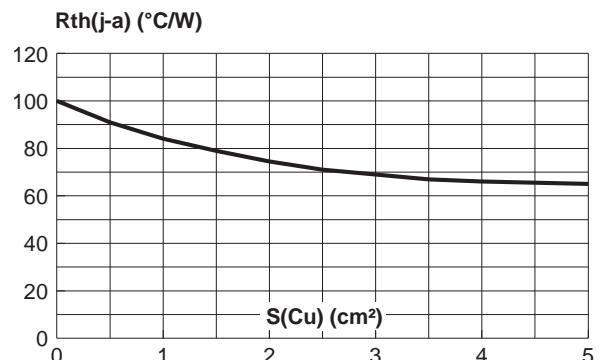
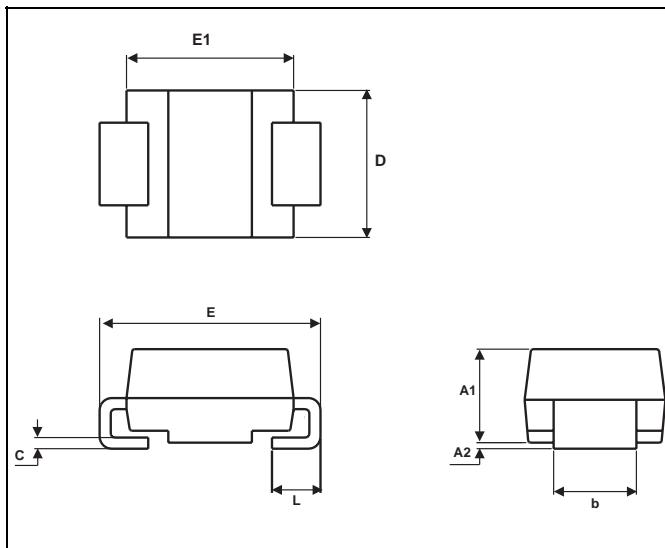


Fig. 12: Thermal resistance junction to ambient versus copper surface under each lead (Epoxy printed circuit board FR4, copper thickness: 35 μm)



PACKAGE MECHANICAL DATA

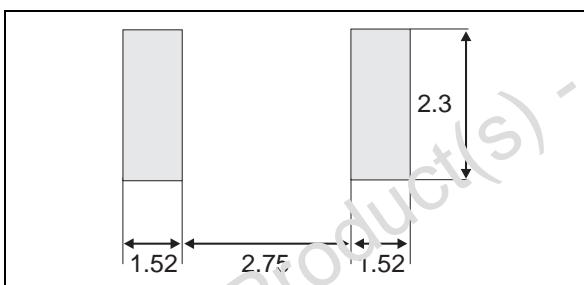
SMB



REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A1	1.90	2.45	0.075	0.096
A2	0.05	0.20	0.002	0.008
b	1.95	2.20	0.077	0.087
c	0.15	0.41	0.006	0.016
E	5.10	5.60	0.201	0.220
E1	4.05	4.60	0.159	0.181
D	3.30	3.95	0.130	0.156
L	0.75	1.60	0.030	0.063

FOOT PRINT DIMENSIONS (in millimeters)

SMB (Plastic)



Ordering type	Marking	Package	Weight	Base qty	Delivery mode
SMBYW01-200	B20	SMB	0.11g	2500	Tape & reel

- Band indicates cathode
- Epoxy meets UL94, V0

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